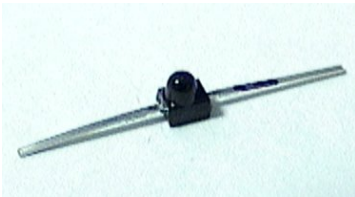


1.9mm Round Subminiature Axial Phototransistor PT91-21B



Features

- Fast response time
- High photo sensitivity
- Small junction capacitance
- Compatible with infrared and vapor phase reflow solder process.
- Pb free
- RoHS Compliance
- The product itself will remain within RoHS compliant version.

Descriptions

- PT91-21B is a phototransistor in miniature SMD package which is molded in black transparent epoxy with spherical top view lens. The device is spectrally matched to infrared emitting diode.

Applications

- Miniature switch
- Counters and sorter
- Position sensor
- Infrared applied system

Device Selection Guide

Part Category	Chip Material	Lens Color
PT	Silicon	Black

Technical drawing of a 2N4350 JFET showing top and side views with dimensions and labels.

Top View Dimensions:

- Pin 1 diameter: $\phi 1.9 \pm 0.2$
- Pin 2 diameter: 2.5 ± 0.1
- Pin 1 to Pin 2 distance: 0.5 ± 0.1
- Pin 2 to Pin 3 distance: 0.4 ± 0.1
- Pin 3 diameter: 2.2 ± 0.2

Side View Dimensions:

- Pin 1 to Pin 2 distance: 7.0 min.
- Pin 2 to Pin 3 distance: 1.1 ± 0.2
- Pin 3 to Pin 4 distance: 1.4 ± 0.2
- Pin 4 to Pin 5 distance: 7.0 min.
- Pin 1 to Pin 2 distance: 0.15 ± 0.05
- Pin 2 to Pin 3 distance: $R0.8 \pm 0.1$
- Pin 3 to Pin 4 distance: 0.65 ± 0.1
- Pin 4 to Pin 5 distance: 1.4 ± 0.1
- Pin 5 to Pin 6 distance: 1.3 ± 0.1
- Pin 6 to Pin 7 distance: 2.7 ± 0.2
- Pin 7 to Pin 8 distance: 0.75 ± 0.1

Labels:

- ① Collector
- ② Emitter

.All dimensions are in millimeters
 .Tolerances unless dimensions $\pm 0.1\text{mm}$

Absolute Maximum Ratings (Ta=25 °C)

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Collector-Voltage	V_{ECO}	5	V
Collector Current	I_C	20	mA
Operating Temperature	T_{opr}	-25 ~ +85	
Storage Temperature	T_{stg}	-40 ~ + 85	
Soldering Temperature *1	T_{sol}	260	
Power Dissipation at(or below) 25 Free Air Temperature	P_d	75	mW

Notes: *1:Soldering time 5 seconds.

Electro-Optical Characteristics (Ta=25)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Rang Of Spectral Bandwidth	0.5		730	---	1100	nm
Wavelength Of Peak Sensitivity	λ_p	---	---	940	---	nm
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=100\mu A$ $E_e=0mW/cm^2$	30	---	---	V
Emitter-Collector Breakdown Voltage	BV_{ECO}	$I_E=10\mu A$ $E_e=0mW/cm^2$	5	---	---	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2mA$ $E_e=1mW/cm^2$	---	---	0.4	V
Collector Dark Current	I_{CEO}	$V_{CE}=20V$ $E_e=0mW/cm^2$	---	---	100	nA
On State Collector Current	$I_{C(ON)}$	$V_{CE}=5V$ $E_e=1mW/cm^2$	1.0	3.0	---	mA

业务技术咨询：TEL/微信: 13422876592

Typical Electro-Optical Characteristics Curves

Fig.1 Spectral Sensitivity

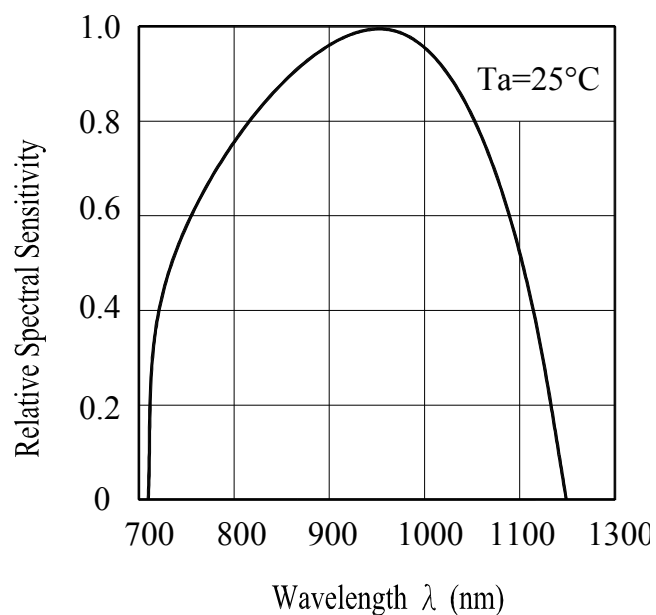


Fig.2 Collector Current vs. Irradiance

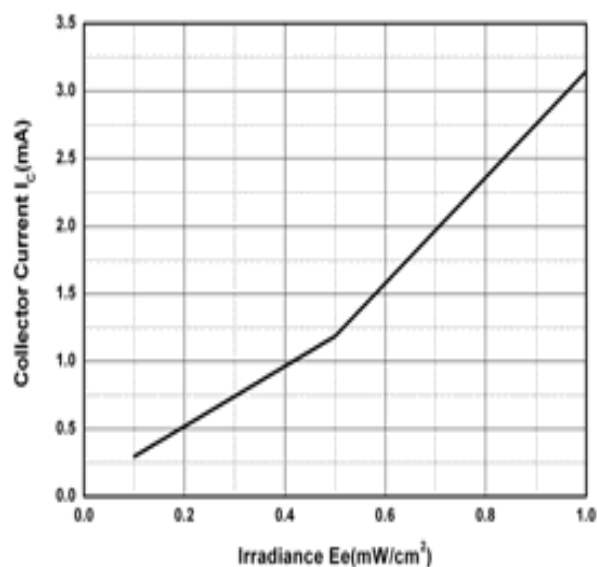
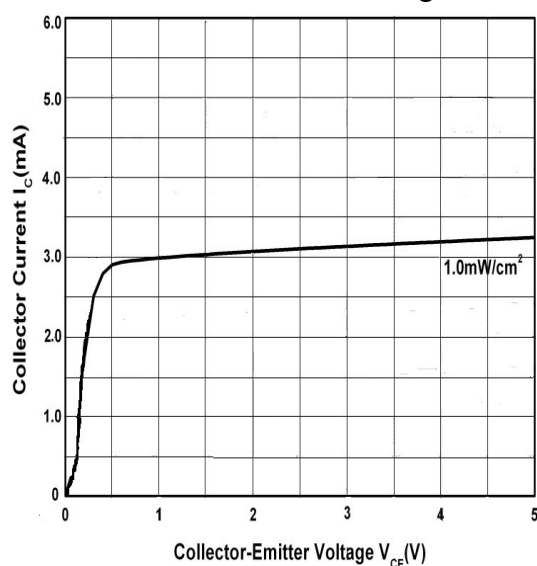


Fig.3 Collector Current vs. Collector-Emitter Voltage



Precautions For Use

1. Over-current-proof

Customer must apply resistors for protection , otherwise slight voltage shift will cause big current change (Burn out will happen).

2. Storage

2.1 Do not open moisture proof bag before the products are ready to use.

2.2 Before opening the package, the Phototransistor should be kept at 30 °C or less and 90%RH or less.

2.3 The Phototransistor should be used within a year.

2.4 After opening the package, the Phototransistor should be kept at 30 °C or less and 60%RH or less.

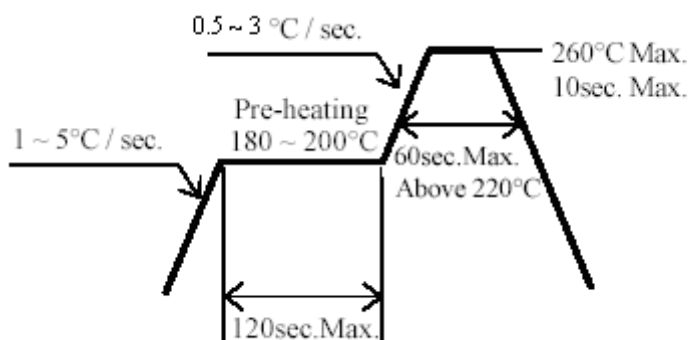
2.5 The Phototransistor should be used within 168 hours (7 days) after opening the package.

2.6 If the moisture absorbent material (silica gel) has faded away or the Phototransistor have exceeded the storage time, baking treatment should be performed using the following conditions.

Baking treatment : 60 ± 5 °C for 24 hours.

3. Soldering Condition

3.1 Pb-free solder temperature profile



3.2 Reflow soldering should not be done more than two times.

3.3 When soldering, do not put stress on the Phototransistor during heating.

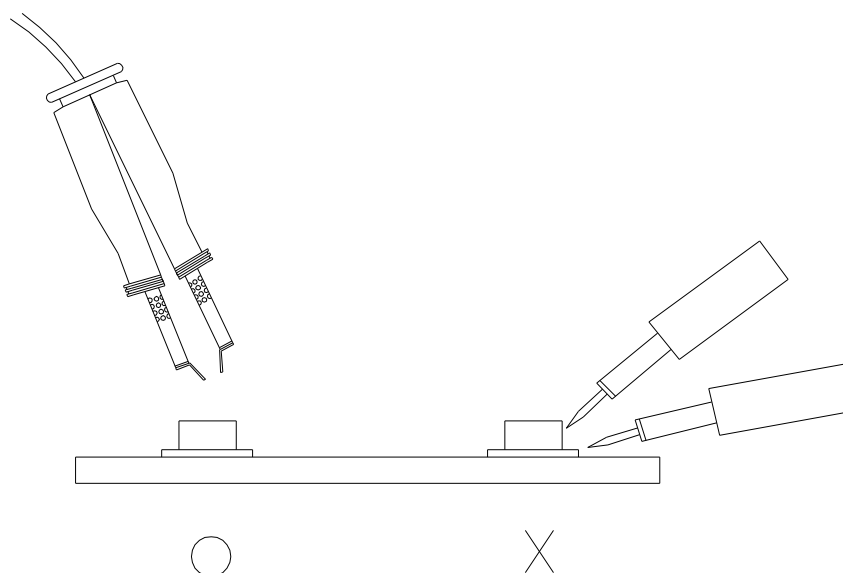
3.4 After soldering, do not warp the circuit board.

4.Soldering Iron

Each terminal is to go to the tip of soldering iron temperature less than 350 for 3 seconds within once in less than the soldering iron capacity 25W. Leave two seconds and more intervals, and do soldering of each terminal. Be careful because the damage of the product is often started at the time of the hand solder.

5.Repairing

Repair should not be done after the Phototransistor have been soldered. When repairing is unavoidable, a double-head soldering iron should be used (as below figure). It should be confirmed beforehand whether the characteristics of the Phototransistor will or will not be damaged by repairing.



Packing Quantity Specification

1000PCS/1Bag

Label Form Specification



CPN: Customer's Production Number

P/N : Production Number

QTY: Packing Quantity

CAT: Ranks

HUE: Peak Wavelength

REF: Reference

LOT No: Lot Number

Notes

1. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification.
2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
3. These specification sheets include materials protected under copyright of EVERLIGHT corporation. Please don't reproduce or cause anyone to reproduce them without EVERLIGHT's consent.

EVERLIGHT ELECTRONICS CO., LTD.
Office: No. 6-8, Zhonghua Rd., Shulin Dist.,
New Taipei City 23860, Taiwan

Tel: 886-2-2685-6688
Fax: 886-2685-2699 , 6897
<http://www.everlight.com>